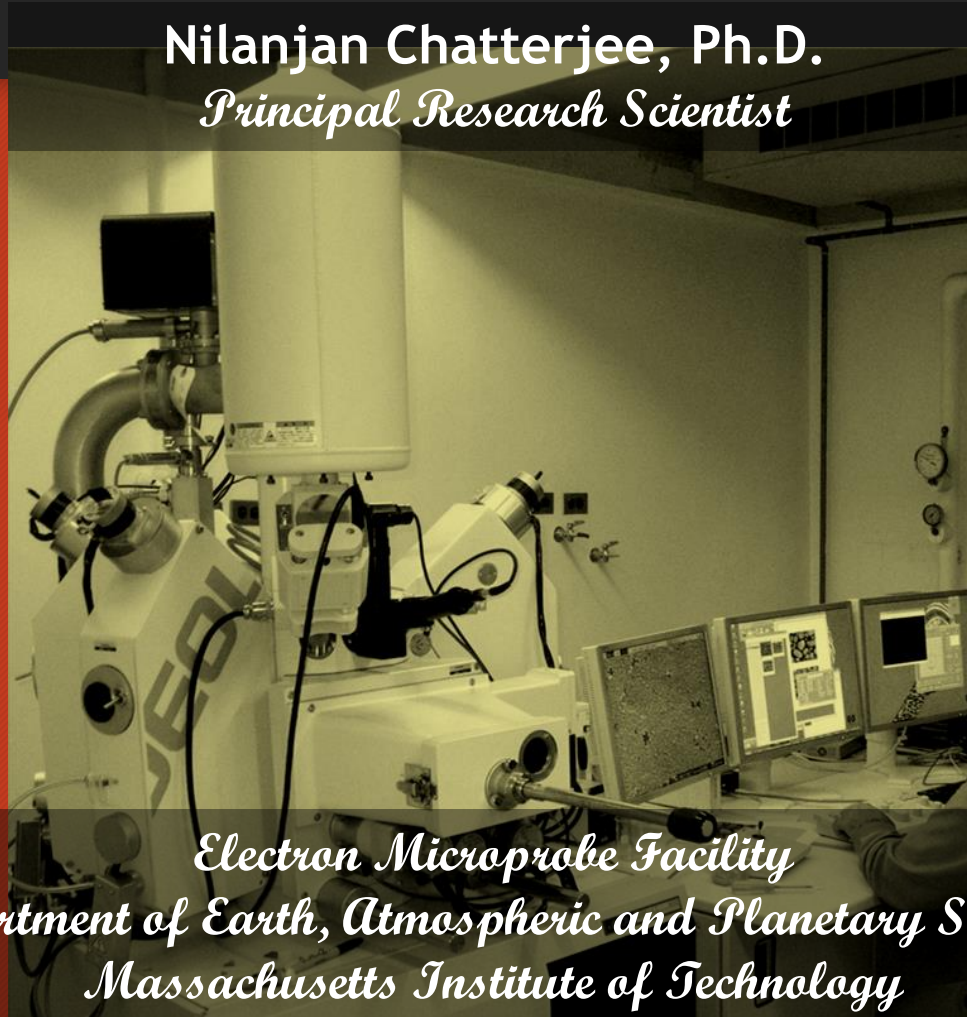


Electron Probe Micro-Analysis (EPMA)

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Uses of the EPMA

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Complete quantitative chemical analysis at micron-scale spatial resolution:

- *Be to U (10-50 ppm minimum detection limit)*

High resolution imaging:

- *compositional contrast (**back-scattered electron**)*
- *surface relief (**secondary electron**)*
- *spatial distribution of elements (**x-ray**)*
- *trace elements, defects (**light**)*

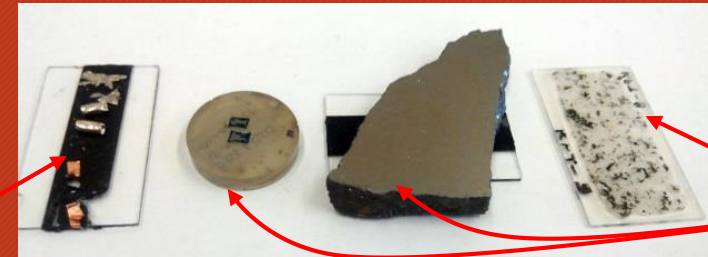
Sample preparation

3

- Sample **cut and mounted** in epoxy, if necessary
- **Coarse polished** with 240-600 SiC paper (53-16 μm)
- **Fine polished** with alumina slurry or diamond paste on cloth (grit size 1.00-0.25 μm)
- **Washed** with water in ultrasonic cleaner after each polishing step, **dried** after final step, **wiped** with ethanol

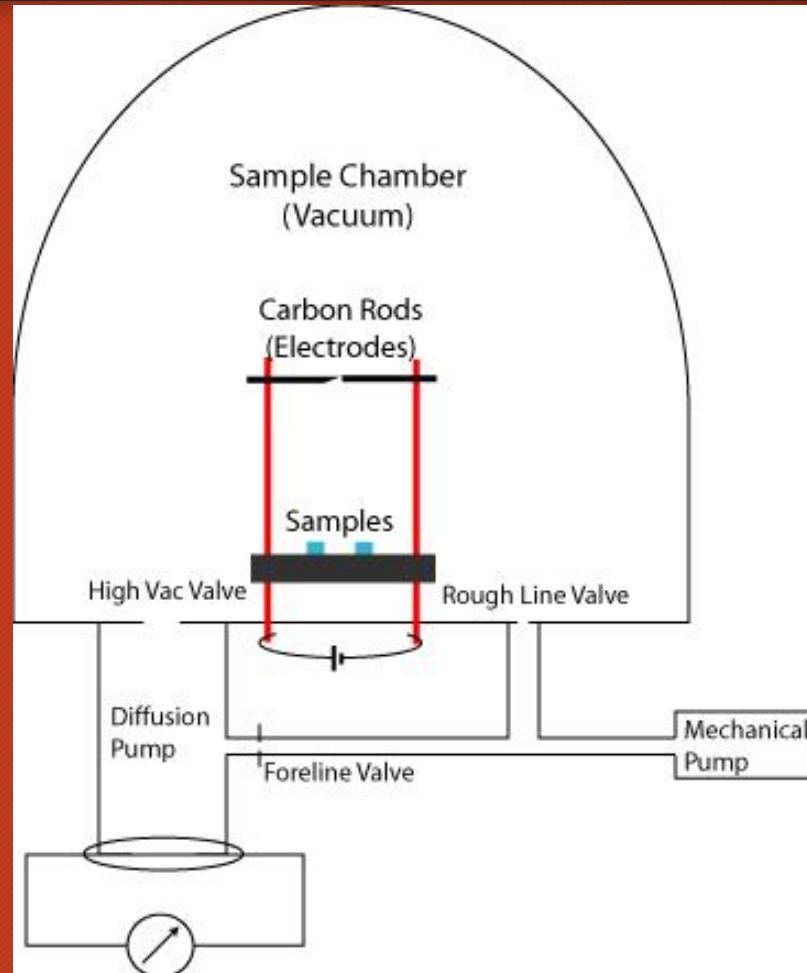
Qualitative analysis

Quantitative analysis

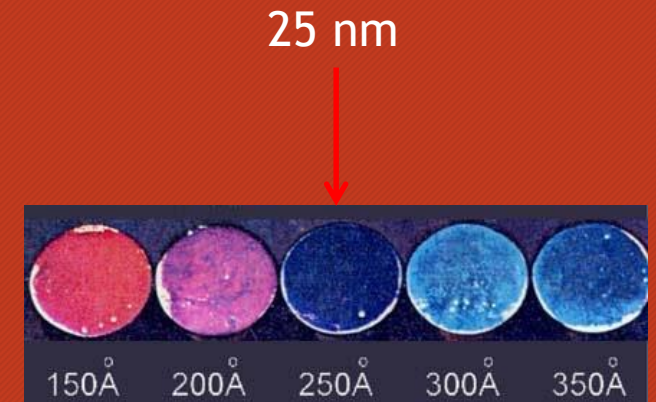


Carbon coating

4



Vacuum evaporator



Thickness is monitored on a polished surface of brass, coated with the samples

JEOL JXA-8200 Superprobe

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Liquid nitrogen for EDS

Energy dispersive
X-ray spectrometer (EDS)

Optical microscope

Sample exchanging
chamber

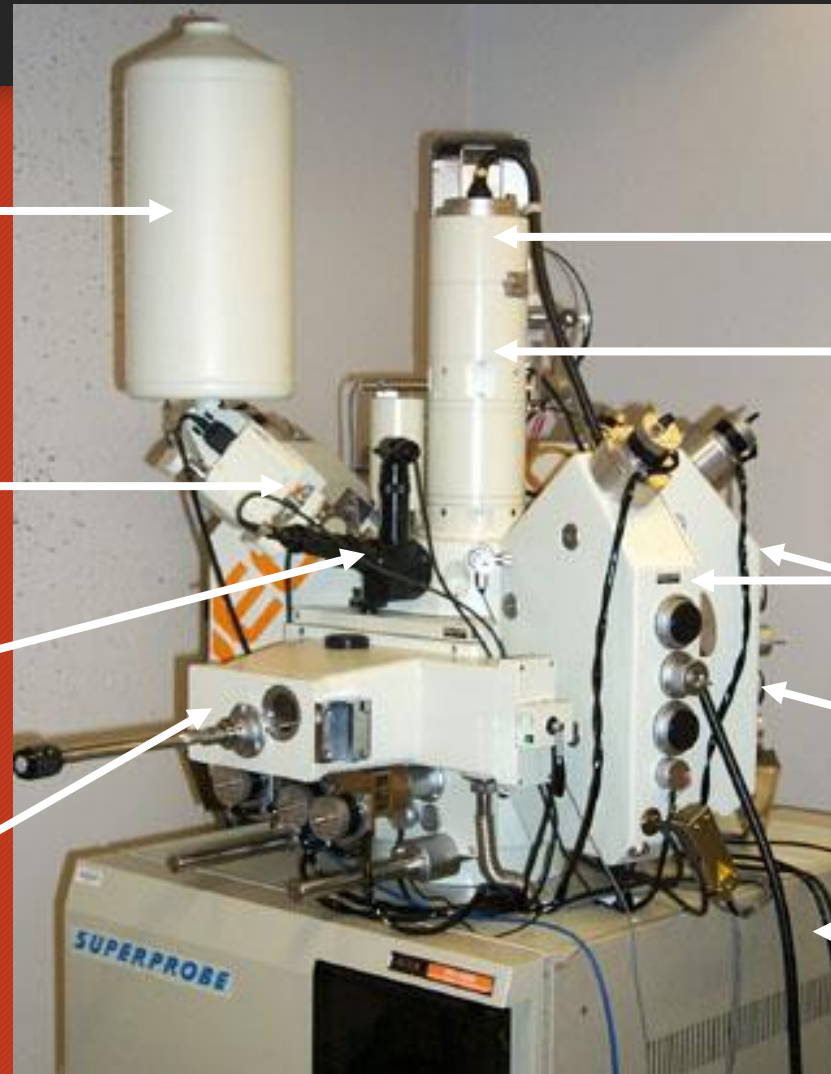
Electron gun

Electron beam column

Wavelength dispersive
X-ray spectrometer (WDS)

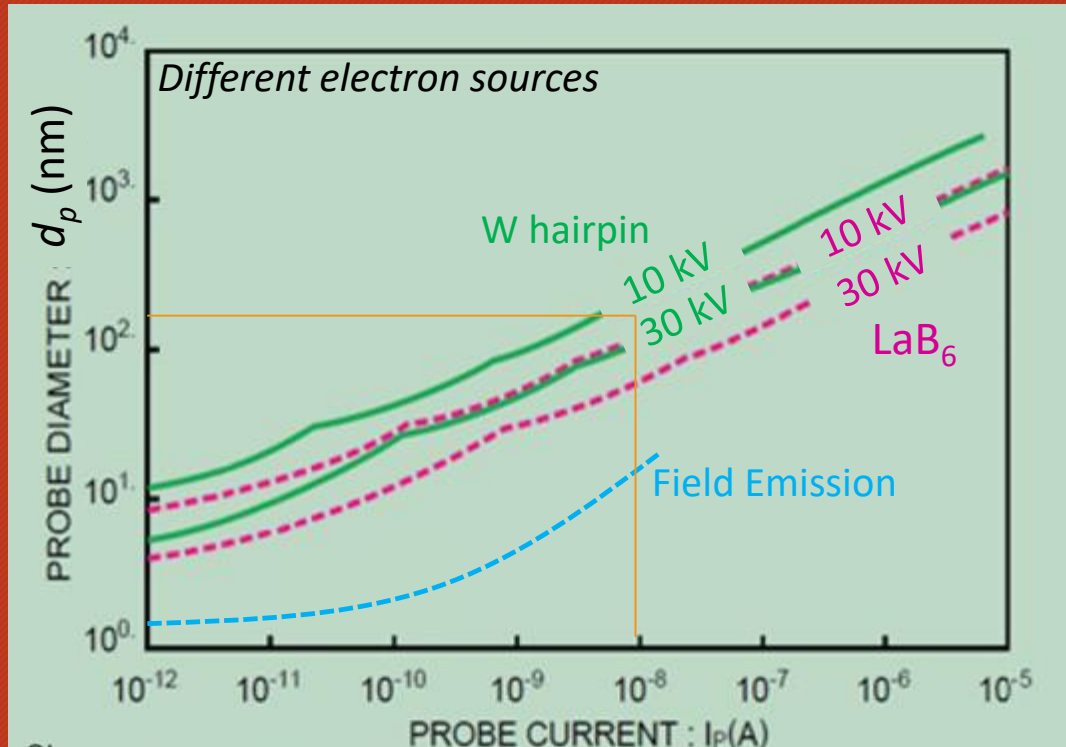
Secondary electron detector

High vacuum pump
(inside)

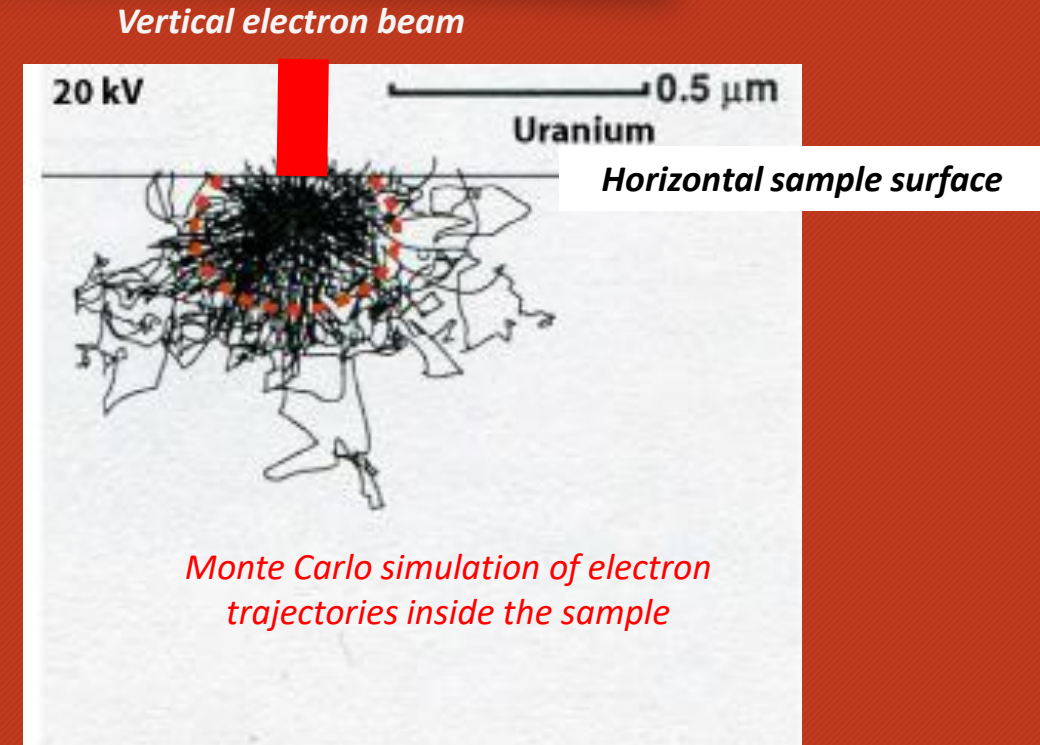


Spatial resolution (spot size) of analysis

6



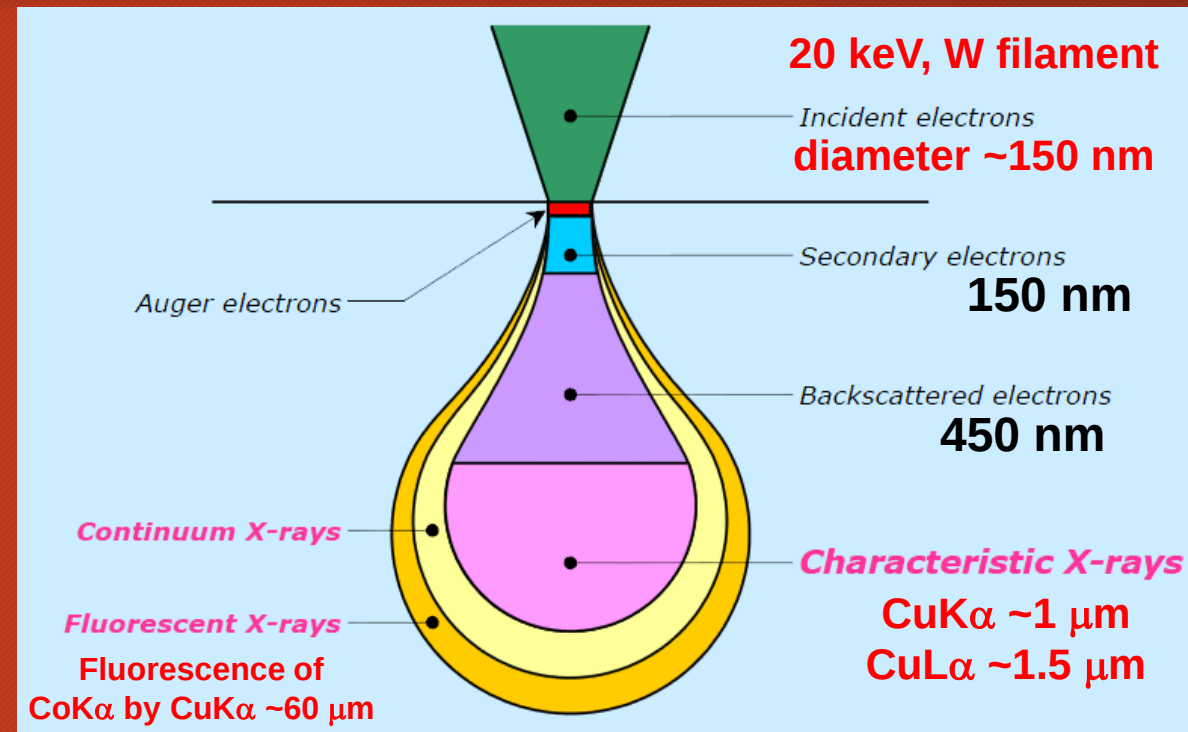
Tungsten hairpin, 15 kV, 10 nA, $d_p \approx 100$ nm



Width of interaction volume $\gg$ probe diameter

Spatial resolution for different signals

7



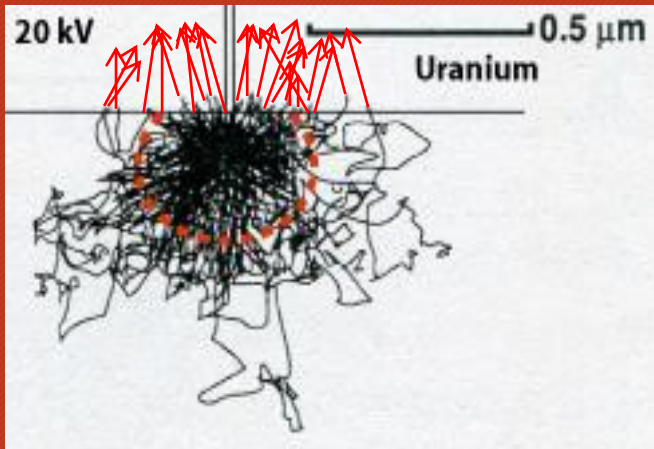
(not to scale)

Production volume for different signals is different

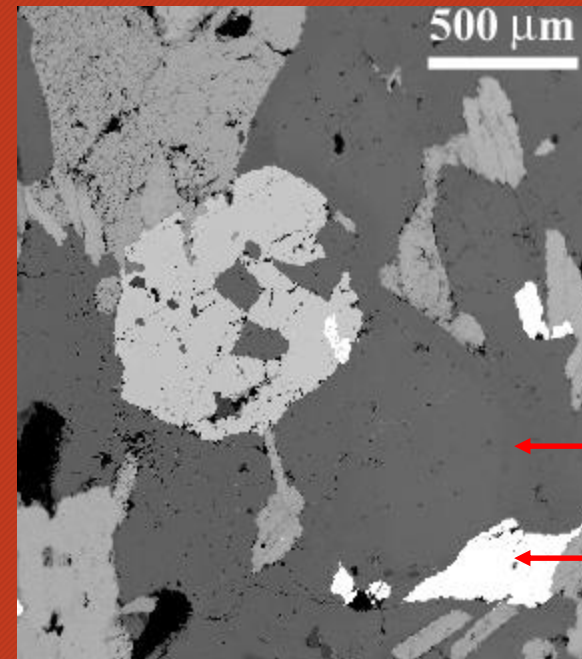
*The “onion shell” model:
Cu-10%Co alloy*

Back-scattered electron (BSE)

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*Beam electrons are
scattered backward*



Light elements

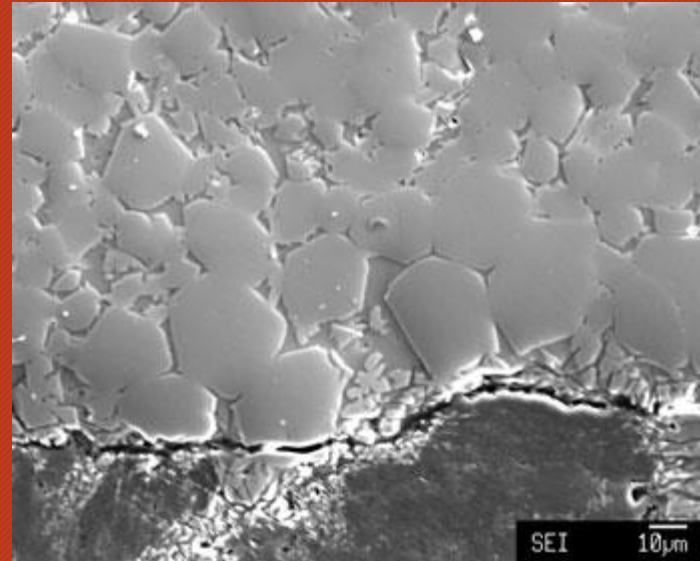
Heavy elements

Compositional contrast

Secondary electron (SE)

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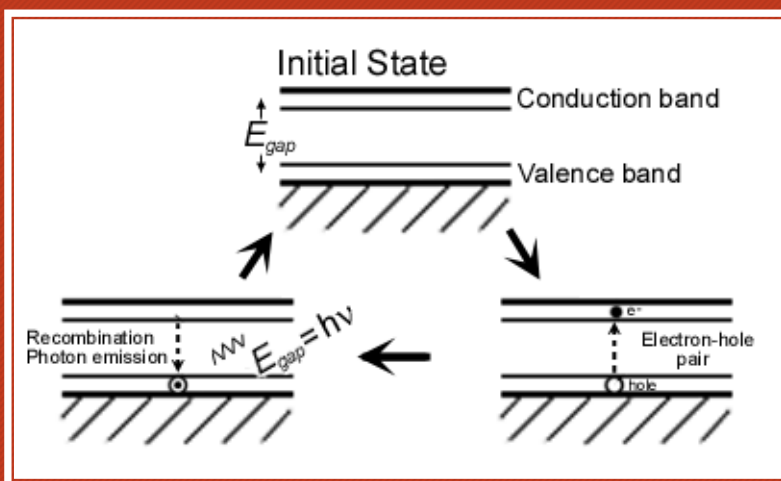
*Produced by ionization
of the target atoms due
through interaction with
the electron beam*



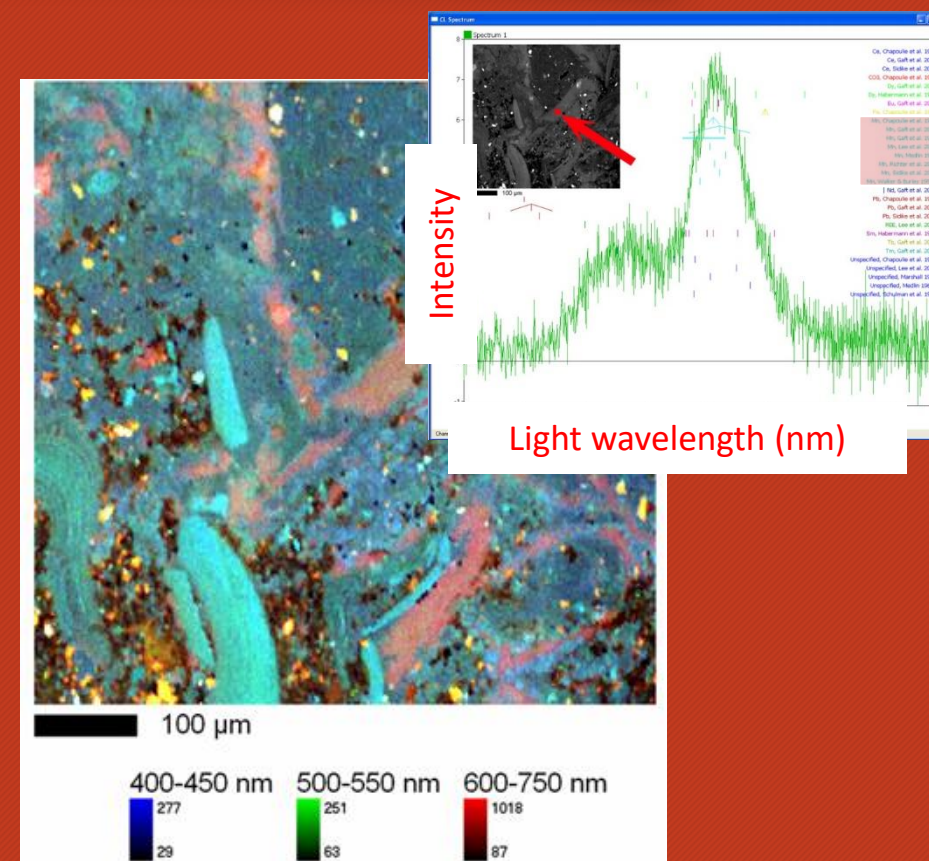
Topographic contrast

Cathodoluminescence (CL)

10



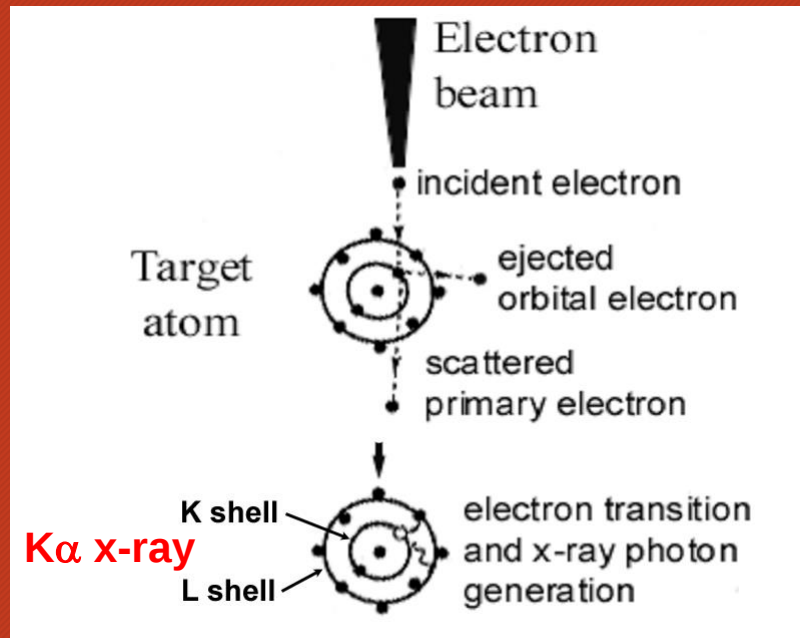
*Light generation
in semiconductors*



Trace impurities generate different light

Characteristic X-ray generation

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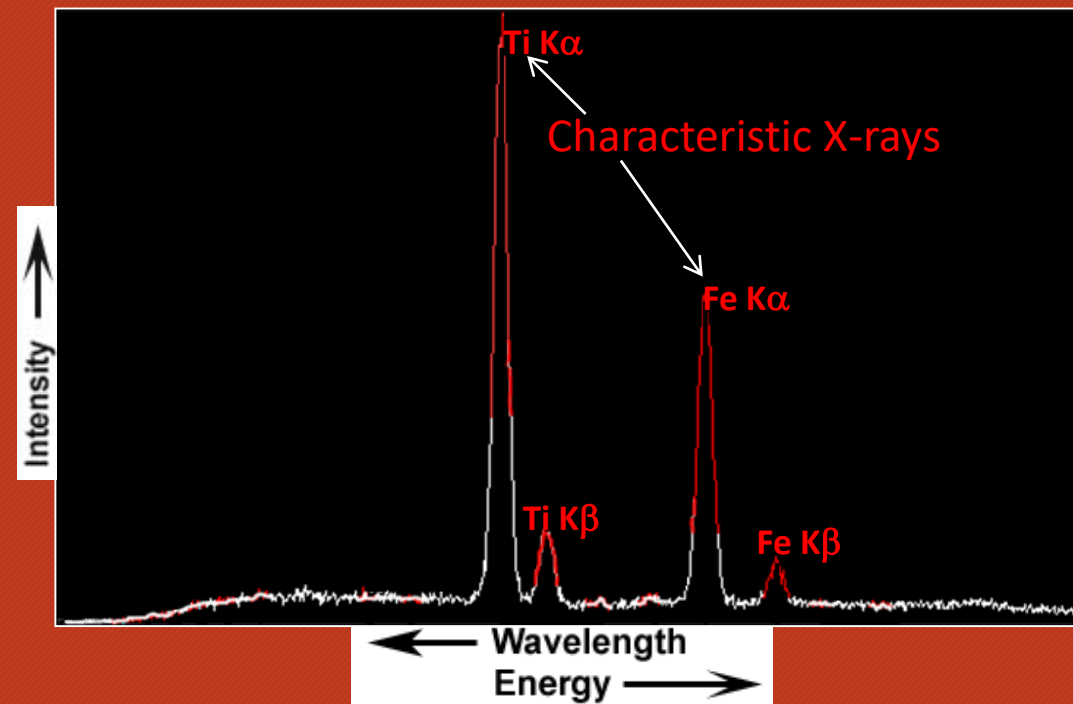


Inner-shell ionization

Overvoltage, $U = E/E_c > 1$

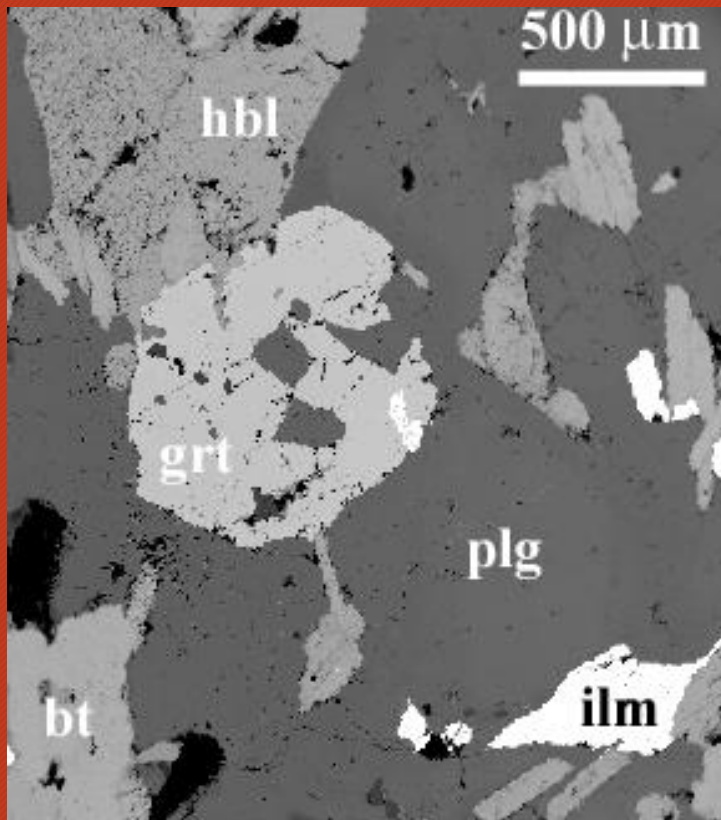
E : electron beam energy

E_c : critical excitation energy
of shell in target atom

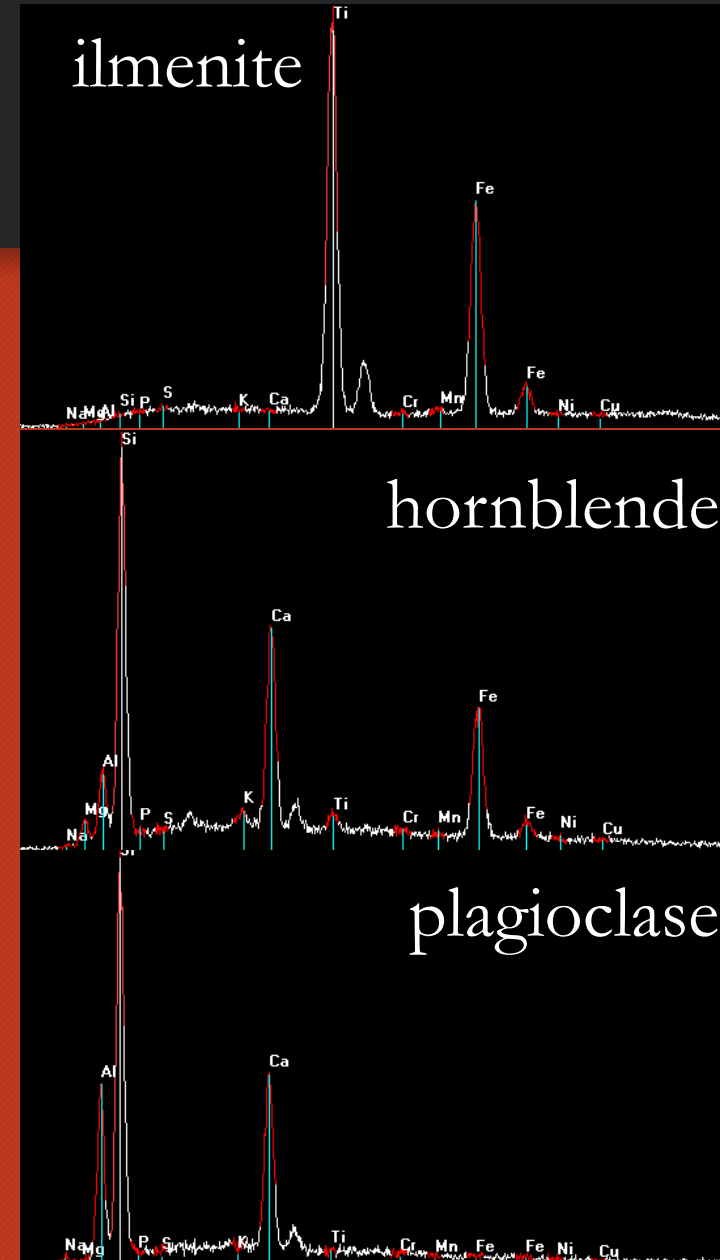


Qualitative analysis with BSE and EDS

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Mean Atomic Number ↑



Wavelength Dispersive Spectrometer (WDS)

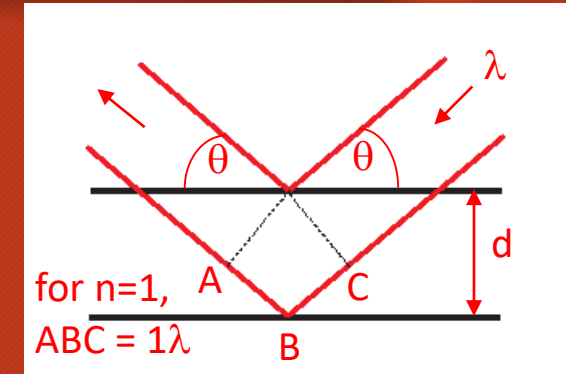
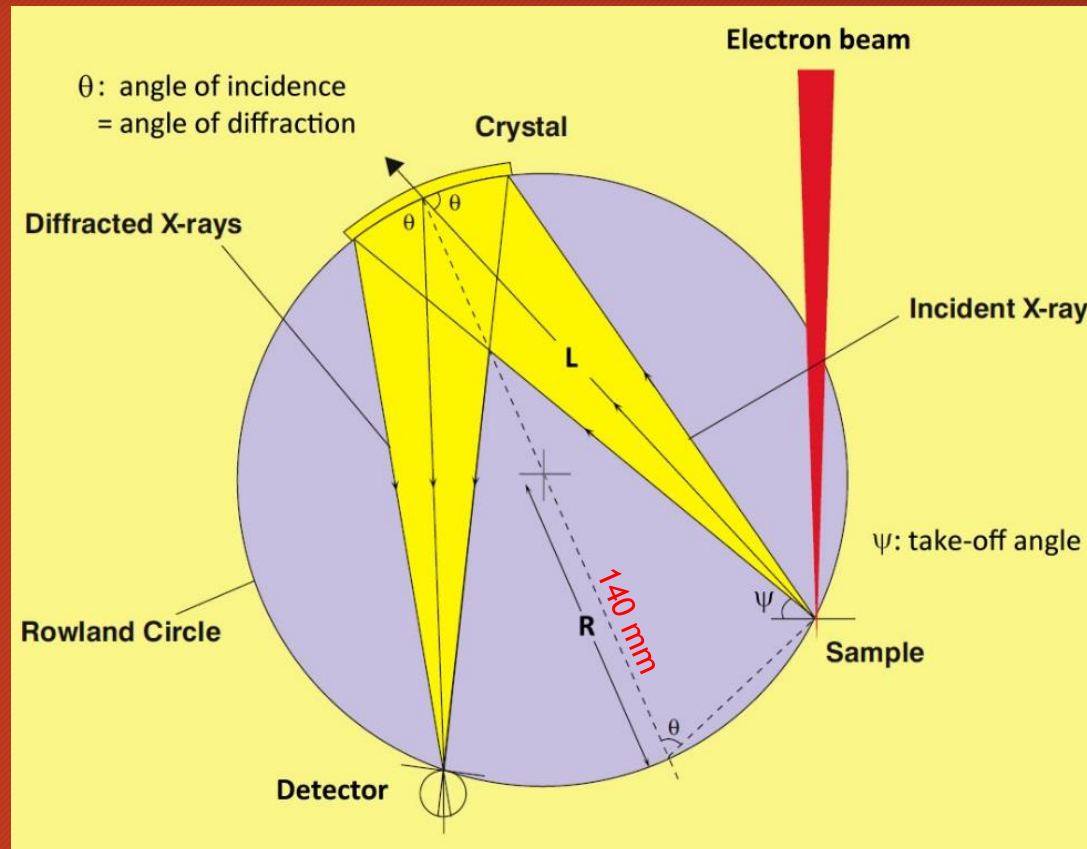
13

$$\sin \theta = \frac{L}{2R}$$

θ : angle of incidence
or diffraction

L: distance between
sample and crystal
 $= n\lambda (R/d)$

R: radius of focusing
(Rowland) circle



Bragg's Law:

$$n\lambda = 2d \sin \theta$$

n : order of diffraction

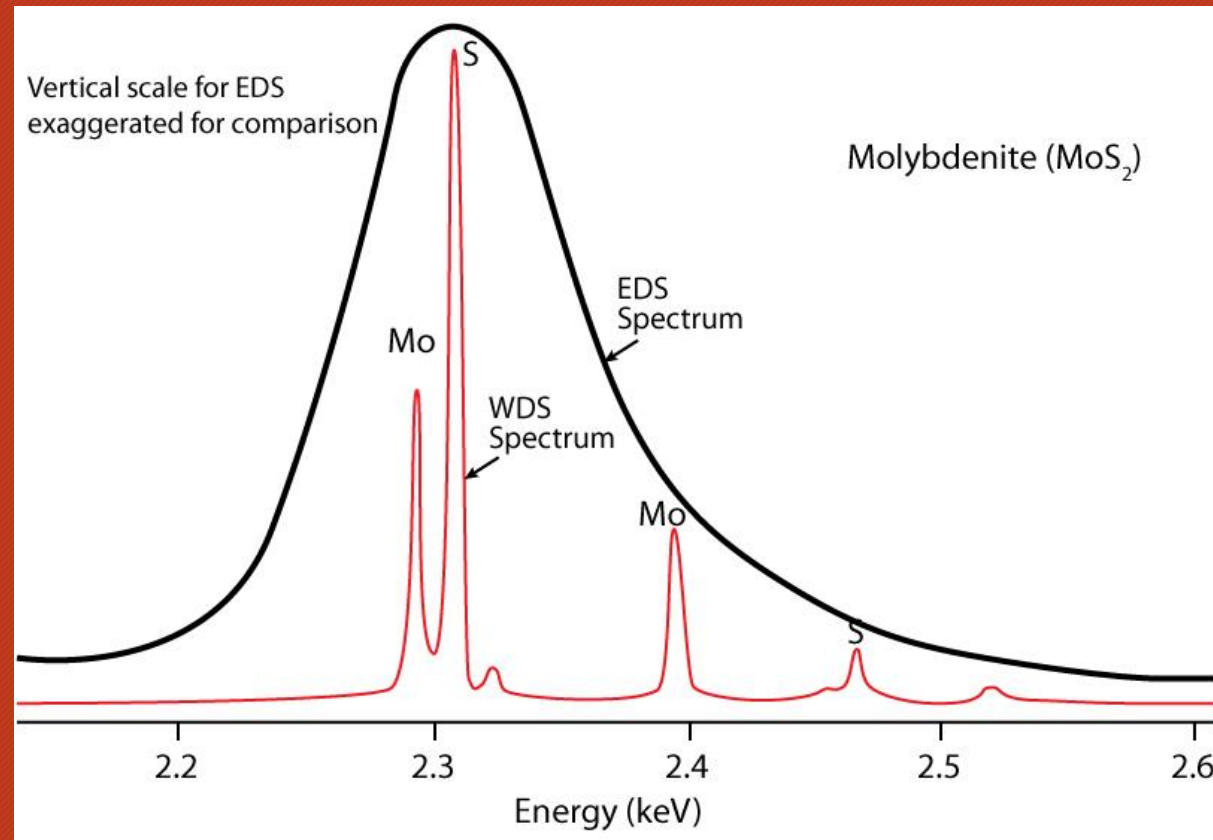
λ : wavelength of X-ray

d : lattice spacing in
diffracting crystal

θ : angle of incidence or
diffraction

WDS vs. EDS spectral resolution

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Peak resolution

with WDS (FWHM ~10 eV)

with EDS (FWHM ~150 eV)

EPMA Quantitative analysis

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X-ray intensity is proportional to the concentration, $C \propto I$

$$\frac{C_i}{C_{(i)}} \propto \frac{I_i}{I_{(i)}}$$

C_i , I_i : concentration and intensity in sample

$C_{(i)}$, $I_{(i)}$: concentration and intensity in standard

$$\frac{I_i}{I_{(i)}} = k_i \text{ (k - ratio)}$$

$$\frac{C_i}{C_{(i)}} = k_i \cdot [\text{ZAF}]_i$$

ZAF Matrix corrections:

Z: Atomic Number correction

A: Absorption correction

F: Fluorescence correction

EPMA Analytical procedure

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- Sample preparation (mounting, polishing, carbon coating)
Carbon coating non-conducting material
- Setting up the Electron Microprobe
Accelerating voltage, beam current, probe diameter, WDS crystal/proportional counters, counting time for each element
- Qualitative analysis with EDS
If nothing is known about the chemical composition
- Measurement of X-ray intensities in standards (**calibration**) by WDS
- Measurement of X-ray intensities in the specimen by WDS and data reduction
Matrix corrections

Typical quantitative analysis output

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		k-ratio	Element Wt%		Oxide Wt%		Atomic proportion	
Element		k-Ratio	El-Wt%	MDLeI%	Ox-Wt%	MDLox%	At-Prop	Error%
SiO ₂	Ka	0.9119	17.30	0.03	37.01	0.05	2.960	0.68%
TiO ₂	Ka	0.0021	0.13	0.05	0.22	0.09	0.013	20.28%
Al ₂ O ₃	Ka	0.5200	11.46	0.03	21.66	0.05	2.042	0.86%
Cr ₂ O ₃	Ka	0.0000	0.00	0.06	0.00	0.08	0.000	99.00%
FeO	Ka	1.0431	21.43	0.07	27.57	0.09	1.844	1.58%
MnO	Ka	0.0809	2.89	0.08	3.73	0.11	0.253	4.29%
MgO	Ka	0.0781	1.36	0.02	2.26	0.04	0.269	2.93%
CaO	Ka	0.3565	5.20	0.04	7.28	0.05	0.624	1.82%
Na ₂ O	Ka	0.0011	0.01	0.04	0.02	0.05	0.003	99.00%
O			39.95				12.000	
Total:			99.75		99.75	Cation:	8.007	

 Minimum detection limit (El-Wt%)
  Minimum detection limit (Ox-Wt%)
  Cation Sum based on a certain #O
  Uncertainty

Types of errors and counting statistics

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Systematic Error

Fixed (but unknown) offsets in all measurements

Low systematic error: high accuracy

Random Error

Fluctuations in each measurement

Low random error: high precision

For N counts, $N \pm \sqrt{N}$

i.e., the uncertainty is $\frac{\sqrt{N}}{N} \times 100$, or $\frac{1}{\sqrt{N}} \times 100 \%$

The percent uncertainty decreases as N increases (more precise)

E.g., uncertainty for 25 counts is 20%

for 100 counts is 10%

for 10,000 counts is 1%

Imaging and mapping modes

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- *Screen capture of beam rastered BSE and SE images:*
 - *fast, high resolution and high quality*
- *Simultaneous mapping with BSE (or SE), CL, and elemental x-rays:*
 - *Beam-raster mode (may have defocusing issues)*
 - *Stage mode: stage moves under electron beam (preferred for large areas)*

Map (image) quality and acquisition times

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- ❑ Image resolution:
number of points measured within the imaged area
- ❑ X-ray Signal:
beam current and counting (dwell) time per point

Acquisition time:

- *Screen capture: 1-2 minutes*
- *Simultaneous mapping: Dwell time x Number of pixels + Stage movement time*

E.g., Time required to map 1 cm x 1 cm area at 10 micron resolution
(1000 x 1000 pixels) using a 25 millisec dwell time
= 25 x 1000,000 millisec + time for stage movement
= ~7 hours + 1 hour (approximately 8 hours, or 0.03 sec/pixel)

Combined BSE, CL and X-ray mapping

